

Journal of Alloys and Compounds 317-318 (2001) 320-323



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Isothermal cross-section of the Ce-Pd-Si phase diagram at 600°C

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Abstract

The interaction of the components in the Ce–Pd–Si system at 600°C was investigated over the whole concentration range by X-ray powder and single crystal diffraction, DTA, and X-ray microprobe analysis. The formation of the two previously reported phases, CePd₂Si and Ce₂Pd₃Si₅, was not confirmed. There are ten ternary compounds in the Ce–Pd–Si system. The crystal structures of seven of them were determined. © 2001 Published by Elsevier Science B.V.

Keywords: Rare earth compounds; Phase equilibria; Ternary system

1. Introduction

The ternary compounds RE-TM-X (RE=rare earth, TM=transition metal, X=Si or Ge) are known to exhibit a number of interesting properties such as heavy-fermion superconductivity, Kondo behavior, anomalous magnetism, and/or intermediate valency. Ternary system Ce-Pd-Si is notable for Kondo-lattice phase Ce₃Pd₂₀Si₆, which was found and studied in earlier researches [1–3]. It was established that this compound displays the unique low-temperature properties [2,3].

The aim of the present investigation was to obtain data about the interaction of the components in the Ce–Pd–Si ternary system in the whole concentration range and about the crystal structure of new ternary intermetallic compounds.

The three binary systems bounding the ternary system have been described in detail in the literature. In reference [4] the Ce–Si binary system is reported as a review of the all previous works, in which this binary system was investigated in whole concentration range by X-ray powder diffraction, DTA and metallographic analyses. Six intermediate phases were found in this work: Ce₅Si₃, Ce₃Si₂, Ce₅Si₄, CeSi, Ce₃Si₅, and CeSi_{2-x}. Except CeSi_{2-x} all intermediate binary phases have a fixed composition. The homogeneity range of CeSi_{2-x} stretches from 63.5 to 66.7 at. % Si. According to Munitz et al. [4], at 600°C, cerium and silicon do not dissolve any noticeable amount of the second component. Crystal structure and lattice parameter

data for the binary phases of the Ce-Si system are summarized in Table 1 [4].

All previous reports about the interaction of the components in the Ce–Pd binary system were summarized and analyzed in the Okamoto's review [5]. There are eight intermediate phases in the Ce–Pd system [5]: Ce₇Pd₃, Ce₃Pd₂, CePd, Ce₃Pd₄, Ce₃Pd₅, CePd₃, CePd₅, CePd₇. Two of these, CePd and CePd₅, have low- and hightemperature modifications (α and β) of their of crystal structure.

At 600°C both exist in their low-temperature modifications. Palladium dissolves up to 13 at.% Ce at 1075°C. Cerium does not dissolve any noticeable amount of palladium. As derived from the X-ray powder diffraction and microstructure data, the homogeneity region of CePd₃ is about 1.4 at.% [5,6]. The other intermediate phases have fixed compositions. In our work the solubility of cerium in palladium at 600°C is about 9 at.%. The homogeneity regions of the other intermediate phases are in accordance with literature data. Crystal structure and lattice parameters data for the binary phases of the Ce–Pd system are summarized in Table 2 [5].

The last detailed study on Pd–Si binary phase diagram was reported in Ref. [7]. This careful experimental work took into account the previous data summarized in [8]. According to [7] at 600°C there are seven binary intermediate phases Pd₈₄Si₁₆, Pd_{82.3}Si_{17.7}, Pd₃Si, Pd_{66.7}Si_{33.3}, Pd_{66.5}Si_{33.5}, Pd_{66.1}Si_{33.9}, Pd_{65.5}Si_{34.5} in the Pd–Si system. The crystal structures are known for Pd₃Si (Fe₃P structural type, *Pnma*, *a*=0.5735 nm, *b*=0.7555 nm *c*=0.5260 nm [9]) and Pd_{66.5}Si_{33.5}, which corresponds to earlier reported Pd₂Si (Fe₂P structural type, *P62m*, *a*=0.6528 nm, *c*=

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Table 1 Crystal structure and lattice parameter data for the intermediate phases in the Ce–Si system [4]

Phase	Composition, at.% Si	Space group	Prototype	Lattice parameters, nm		
				a	b	с
Ce ₅ Si ₃	37.5	I4/mcm	W ₅ Si ₃	0.7868		1.373
Ce ₃ Si ₂	40	P4/mbm	U ₃ Si ₂	0.780		0.434
Ce ₅ Si ₄	44.4	$P4_{1}2_{1}2$	Zr_5Si_4	0.793		1.504
CeSi	50	Pnma	FeB	0.8302	0.3962	0.5964
Ce ₃ Si ₅	62.5	Imma	α -GdSi ₂	0.4192	0.413	1.392
CeSi _{2-x}	63.5 to 66.7	$I4_1/amd$	a-ThSi ₂	0.4192		1.390

Table 2 Crystal structure and lattice parameter data for the intermediate phases in the Ce–Pd system [5,6]

Phase	Composition, at.% Pd	Space group	Prototype	Lattice parameters, nm		
				a	b	С
Ce ₇ Pd ₃	30	P6 ₃ mc	Fe ₃ Th ₇	1.0222		0.6441
Ce ₃ Pd ₂	40	5	5 /			
α-CePd	50	Cmcm	CrB	0.3890	1.0910	0.4635
β-CePd	50	Pnma	FeB			
Ce_3Pd_{4x}	57.1	RĪ	Pu_3Pd_4	1.3669		0.5824
Ce ₃ Pd ₅	62.5	Pā2m	Th ₃ Pd ₅			
CePd ₃	74.8-76.2	Pm3m	Cu ₃ Au	0.4160		
α-CePd ₅	83.3	Pnma	2	0.5700	0.4062	0.8462
β-CePd ₅	83.3	cubic		0.4055		
CePd ₇	87.5	Fm3m	Pt ₇ Cu	0.80805		

0.3437 nm [9]). The reciprocal solubility of Pd and Si in each other at 600°C is found to be negligible [7].

Systematic studies of the ternary Ce–Pd–Si system through the whole concentration range have not previously been performed. Up to now the following ternary intermetallic compounds were described or mentioned in the literature: $Ce_3Pd_{20}Si_6$ [1–3], $CePd_2Si_2$ [10], $CePd_2Si$ [11], and $Ce_2Pd_3Si_5$ [12].

The crystallographic data that has been published for these four phases are given in Table 3 with references.

2. Experimental details

The present investigation was done with 117 samples having masses of about 1 g. These were made in an electric arc furnace under an argon atmosphere with a nonconsumable tungsten electrode and a water cooled copper hearth. The purity of cerium was 99 at.%, the purity of palladium and silicon was better than 99.9 at.%. Titanium was used as a getter during melting. The alloys were remelted two times in order to achieve complete fusion and homogeneity. Alloys with melting losses not exceeding 1 wt.% were choosen for the experiments. After melting all alloys were subjected to a homogenizing anneal in evacuated double-walled quartz ampoules containing titanium chips as getters. Annealing was done in a resistance furnace at 600°C for 720 h with subsequent quench into ice water.

X-ray powder and monocrystal diffraction, DTA, and electron probe X-ray analyses were used in the present investigation.

Initial phase analyses were performed with an URS-60 generating unit with Cr K_{α} radiation (λ =0.229092 nm) for RKD-57 cameras having asymmetric film loading. For

Table 3

Crystal structure and lattice parameter data published for the ternary intermediate phases of the Ce-Pd-Si system

Phase	Space group	Prototype	Lattice parameters, nm			Ref.
			a	b	С	
Ce ₃ Pd ₂₀ Si ₆	Fm3m	Ce ₃ Pd ₂₀ Ge ₆	1.2161			[1]
		5 20 0	1.2280			[2]
CePd ₂ Si ₂	I4/mmm	ThCu ₂ Si ₂	0.4232		0.9911	[10]
CePd ₂ Si	Pnma	YPd ₂ Si	0.6877	0.7609	0.5695	[11]
Ce ₂ Pd ₃ Si ₅	Ibam	U ₂ Co ₃ Si ₅				[12]





Fig. 1. Isothermal cross-section of the Ce-Pd-Si system at 600°C.

precision lattice parameters, one or the other of the following was used:

- 'DRON-2.0' with Fe K_{α} radiation, $\lambda = 0.193728$ nm;
- 'DRON-3.0' with Cu K_{α} radiation, $\lambda = 0.154178$ nm;
- FR-552 focusing monochromator camera with Cu $K_{\alpha 1}$ radiation, $\lambda = 0.154051$ nm and Ge as an internal standard.

X-ray monocrystal analyses were first made photographically with RKV-86 camera and Mo K radiation, then with an Enraf-Nonius CAD-4 autodiffractometer and Mo K_{α} radiation. Calculations were performed with the CSDprograms of [13].

Electron probe X-ray analyses were done with a 'Camebax Microbeam' analyzer. This device was used for phase identification of the individual grains in the microstructure by energy dispersive analyses of secondary electrons in combination with determination of the position and intensity of characteristic X-ray wavelengths.

DTA experiments were executed on high temperature VDTA- $8M_2$ equipment (W-W/Re thermocouples) in BeO crucibles. As standards for the calibrating pure Fe, Cu, Pt metals were used.

3. Results and discussion

Results from the present measurements were used in the construction of the isothermal cross-section of the Ce–Pd–Si phase diagram at 600°C (Fig. 1). The ternary phases CePd₂Si and Ce₂Pd₃Si₅ were not found in our study. CePd₅, CePd₃, CePd, Ce₇Pd₃, Ce₅Si₃, CeSi, and CeSi_{2-x} all have noticeable extentions into the ternary system. The homogeneity regions of the other binary phases are negligible.

The interaction of Ce, Pd and Si leads to the formation of at least ten ternary phases stable at 600°C, including the two phases already reported (Table 4). Powder diffraction method was applied for calculating the structure of $CePdSi_3$, $CePd_2Si_2$, $Ce(Pd,Si)_2$, $Ce_4(Pd,Si)_8$, and Ce₃Pd₂₀Si₆. The structures of Ce₈Pd₆₂Si₃₀ and Ce₃Pd₅Si were determined on single crystals. Investigation of the powder diffraction data of three alloys with the approximate compositions Ce45Pd13Si42, Ce33Pd42Si25, and $Ce_{50}Pd_{38}Si_{12}$ leads to the speculation that even more ternary phases may exist at or near these compositions. However, no crystal structure determinations were performed because suitable single crystals were not obtained. The obtained crystallographic data are presented in Table 4.

DTA experiments show the following thermal effects on heating the following samples:

 $Ce_{3}Pd_{20}Si_{6}$ 1240±5°C

$$Ce_3Pd_5Si \quad T_1 = 950 \pm 5^{\circ}C, T_2 = 985 \pm 5^{\circ}C$$

Table 4

Crystal structure and lattice parameter data for the ternary intermediate phases in the Ce-Pd-Si system

N. Phase	Space group	Prototype	Lattice parameters, nm			
			a	b	С	
1. CePdSi ₃	I4 mm	BaNiSn ₃	0.43209(5)		0.9606(2)	
2. $Ce(Pd,Si)_2$	P6/mmm	AlB ₂	0.4219(4)		0.4134(4)	
3. $CePd_2Si_2$	I4/mmm	CeAl ₂ Ga ₂	0.42365(7)		0.9899(3)	
4. $Ce_4(Pd,Si)_8$	$I4_1/amd$	α -ThSi ₂	0.41842(6)		1.4571(3)	
5. $Ce_{45}Pd_{13}Si_{42}$		-				
6. $Ce_8Pd_{62}Si_{30}^{-a}$	Fm3m		1.8010(2)			
7. $Ce_{33}Pd_{42}Si_{25}$						
8. $\operatorname{Ce_3Pd_{20}Si_6}$	Fm3m	$Ce_3Pd_{20}Ge_6$	1.2161(1)			
9. Ce ₃ Pd ₅ Si ₁	Imma	5 20 0	1.3027(4)	0.7377(4)	0.7580(4)	
10. $Ce_{50}Pd_{38}Si_{12}$						

^a Detailed description is in press.

 $Ce_8Pd_{62}Si_{30}$ $T_1 = 1110 \pm 5^{\circ}C, T_2 = 1160 \pm 5^{\circ}C$

 $CePd_2Si_2 = 1510 \pm 10^{\circ}C$

Acknowledgements

This work is supported by the Russian Foundation of Basic Research (grant N 00-03-32651a).

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